

**EXISTING SET OF CLAIMS**

Claims 1 to 23 (Canceled)

24. (Withdrawn) A phosphor of SiC excited by an external light source for emitting light, doped with N and at least one of B and Al.

25. (Withdrawn) The phosphor of SiC according to claim 24, wherein both of the doping concentration with at least one of B and Al and the doping concentration with N are  $10^{15}/\text{cm}^3$  to  $10^{20}/\text{cm}^3$ .

26. (Withdrawn) The phosphor of SiC according to claim 25, wherein both of the doping concentration with at least one of B and Al and the doping concentration with N are  $10^{16}/\text{cm}^3$  to  $10^{20}/\text{cm}^3$ .

27. (Withdrawn) The phosphor of SiC according to claim 24, emitting fluorescence having a wavelength of 500 nm to 750 nm with a peak wavelength in the range of 500 nm to 650 nm.

28. (Withdrawn) The phosphor of SiC according to claim 27, wherein SiC is doped with N and B, the concentration of either N or B is  $10^{15}/\text{cm}^3$  to  $10^{18}/\text{cm}^3$ , and the concentration of either B or N is  $10^{16}/\text{cm}^3$  to  $10^{19}/\text{cm}^3$ .

29. (Withdrawn) The phosphor of SiC according to claim 24, emitting fluorescence having a wavelength of 400 nm to 750 nm with a peak wavelength in the range of 400 nm to 550 nm.

30. (Withdrawn) The phosphor of SiC according to claim 29, wherein SiC is doped with N and Al, the concentration of either N or Al is  $10^{15}/\text{cm}^3$  to  $10^{18}/\text{cm}^3$ , and the concentration of either Al or N is  $10^{16}/\text{cm}^3$  to  $10^{19}/\text{cm}^3$ .

31. (Withdrawn) A method of manufacturing a phosphor of SiC excited by an external light source for emitting fluorescence having a wavelength of 500 nm to 750 nm with a peak wavelength in the range of 500 nm to 650 nm and doped with N and B so that the concentration of either N or B is  $10^{15}/\text{cm}^3$  to  $10^{18}/\text{cm}^3$  and the concentration of either B or N is  $10^{16}/\text{cm}^3$  to  $10^{19}/\text{cm}^3$ ,

by forming an SiC crystal by sublimation recrystallization with a B source of  $\text{LaB}_6$ ,  $\text{B}_4\text{C}$ ,  $\text{TaB}_2$ ,  $\text{NbB}_2$ ,  $\text{ZrB}_2$ ,  $\text{HfB}_2$ , BN or carbon containing B.

32. (Withdrawn) The method of manufacturing a phosphor of SiC according to claim 31, performing thermal annealing at a temperature of at least  $1300^\circ\text{C}$  for at least one hour after sublimation recrystallization or thermal diffusion.

33. (Withdrawn) A method of manufacturing a phosphor of SiC excited by an external light source for emitting fluorescence having a wavelength of 500 nm to 750 nm with a peak wavelength in the range of 500 nm to 650 nm and doped with N and B so that the concentration of either N or B is  $10^{15}/\text{cm}^3$  to  $10^{18}/\text{cm}^3$  and the concentration of either B or N is  $10^{16}/\text{cm}^3$  to  $10^{19}/\text{cm}^3$ ,

by thermally diffusing a B source of simple B,  $\text{LaB}_6$ ,  $\text{B}_4\text{C}$ ,  $\text{TaB}_2$ ,  $\text{NbB}_2$ ,  $\text{ZrB}_2$ ,  $\text{HfB}_2$  or BN into SiC under a vacuum or an inert gas atmosphere at a temperature of at least  $1500^\circ\text{C}$ .

34. (Withdrawn) The method of manufacturing a phosphor of SiC according to claim 33, performing thermal annealing at a temperature of at least  $1300^\circ\text{C}$  for at least one hour after sublimation recrystallization or thermal diffusion.

35. (Withdrawn) The method of manufacturing a phosphor of SiC according to claim 33, removing a surface layer after thermal diffusion.

36. (Withdrawn) A substrate for a semiconductor consisting of a 6H-SiC single-crystalline phosphor excited by an external light source for emitting light and doped with N and at least one of B and Al.

37. (Withdrawn) The substrate for a semiconductor according to claim 36, consisting of a 6H-SiC single-crystalline phosphor doped with N and B for emitting fluorescence having a wavelength of 500 nm to 750 nm with a peak wavelength in the range of 500 nm to 650 nm.

38. (Withdrawn) The substrate for a semiconductor according to claim 36, consisting of a 6H-SiC single-crystalline phosphor doped with N and Al for emitting fluorescence having a wavelength of 400 nm to 750 nm with a peak wavelength in the range of 400 nm to 550 nm.

39. (Withdrawn) A method of manufacturing a substrate for a semiconductor consisting of a 6H-SiC single-crystalline phosphor excited by an external light source for emitting fluorescence having a wavelength of 500 nm to 750 nm with a peak wavelength in the range of 500 nm to 650 nm and doped with N and B so that the concentration of either N or B is  $10^{15}/\text{cm}^3$  to  $10^{18}/\text{cm}^3$  and the concentration of either B or N is  $10^{16}/\text{cm}^3$  to  $10^{19}/\text{cm}^3$ , comprising the steps of:

thermally diffusing a B source of simple B,  $\text{LaB}_6$ ,  $\text{B}_4\text{C}$ ,  $\text{TaB}_2$ ,  $\text{NbB}_2$ ,  $\text{ZrB}_2$ ,  $\text{HfB}_2$  or BN into SiC under a vacuum or an inert gas atmosphere at a temperature of at least  $1500^\circ\text{C}$ ; and removing a surface layer.

40. (Withdrawn) The method of manufacturing a substrate for a semiconductor according to claim 39, performing thermal annealing at a temperature of at least  $1300^\circ\text{C}$  after sublimation recrystallization or thermal diffusion.

41. (Withdrawn) A method of manufacturing a substrate for a semiconductor consisting of a 6H-SiC single-crystalline phosphor excited by an external light source for emitting fluorescence having a wavelength of 500 nm to 750 nm with a peak wavelength in the range of 500 nm to 650 nm and doped with N and B so that the concentration of either N or B is  $10^{15}/\text{cm}^3$  to  $10^{18}/\text{cm}^3$  and the concentration of either B or N is  $10^{16}/\text{cm}^3$  to  $10^{19}/\text{cm}^3$ , wherein

atmosphere gas in crystal growth contains  $\text{N}_2$  gas of 1 % to 30 % in gas partial pressure, and raw material SiC contains 0.05 mol % to 15 mol % of a B source, and an SiC crystal is formed by sublimation recrystallization.

42. (Withdrawn) The method of manufacturing a substrate for a semiconductor according to claim 41, performing thermal annealing at a temperature of at least 1300°C after sublimation recrystallization or thermal diffusion.

43. (Withdrawn) Powder for a semiconductor consisting of a 6H-SiC single-crystalline phosphor excited by an external light source for emitting fluorescence having a wavelength of 500 nm to 750 nm with a peak wavelength in the range of 500 nm to 650 nm, having a particle diameter of 2  $\mu\text{m}$  to 10  $\mu\text{m}$  and a central particle diameter of 3  $\mu\text{m}$  to 6  $\mu\text{m}$ .

44. (Previously Presented) A light-emitting apparatus comprising a substrate for a semiconductor consisting of a 6H-SiC single-crystalline phosphor doped with N and at least one of B and Al and a light-emitting device of a nitride semiconductor formed on said substrate.

45. (Previously Presented) The light-emitting apparatus according to claim 44, wherein the emission wavelength of said light-emitting device of a nitride semiconductor is not more than 408 nm.

46. (Previously Presented) The light-emitting apparatus according to claim 44, wherein both of the doping concentration with at least one of B and Al and the doping concentration with N in said 6H-SiC single-crystalline phosphor are  $10^{16}/\text{cm}^3$  to  $10^{19}/\text{cm}^3$ .

47. (Previously Presented) The light-emitting apparatus according to claim 46, wherein both of the doping concentration with at least one of B and Al and the doping concentration with N in said 6H-SiC single-crystalline phosphor are  $10^{17}/\text{cm}^3$  to  $10^{19}/\text{cm}^3$ .

48. (Previously Presented) A light-emitting apparatus having one or at least two layers consisting of a 6H-SiC single-crystalline phosphor doped with N and at least one of B and Al on a substrate of SiC for a semiconductor and comprising a light-emitting device of a nitride semiconductor on said 6H-SiC single-crystalline phosphor layer(s).

49. (Previously Presented) The light-emitting apparatus according to claim 48, wherein the emission wavelength of said light-emitting device of a nitride semiconductor is not more than 408 nm.

50. (Previously Presented) The light-emitting apparatus according to claim 48, wherein both of the doping concentration with at least one of B and Al and the doping concentration with N in said 6H-SiC single-crystalline phosphor are  $10^{16}/\text{cm}^3$  to  $10^{19}/\text{cm}^3$ .

51. (Previously Presented) The light-emitting apparatus according to claim 50, wherein both of the doping concentration with at least one of B and Al and the doping concentration with N in said 6H-SiC single-crystalline phosphor are  $10^{17}/\text{cm}^3$  to  $10^{19}/\text{cm}^3$ .